

High Efficiency and Low Distortion Internally Matched Power GaAs FETs (C-Band)

Features

- Low intermodulation distortion
 - $IM_3 = -45$ dBc at $P_o = 31.5$ dBm, Single Carrier Level
- High power
 - $P_{1dB} = 42.5$ dBm at 5.9 GHz to 6.4 GHz
- High gain
 - $G_{1dB} = 8.0$ dB at 5.9 GHz to 6.4 GHz
- Broadband internally matched
- Hermetically sealed package

RF Performance Specifications ($T_a = 25^\circ\text{C}$)

Characteristic	Symbol	Condition	Unit	Min.	Typ.	Max.
Output Power at 1dB Compression Point	P_{1dB}	$V_{DS} = 10V$ $f = 5.9 \sim 6.4$ GHz	dBm	41.5	42.5	–
Power Gain at 1dB Compression Point	G_{1dB}		dB	7.0	8.0	–
Drain Current	I_{DS}		A	–	4.4	5.0
Gain Flatness	ΔG		dB	–	–	± 0.8
Power Added Efficiency	η_{add}		%	–	34	–
3rd Order Intermodulation Distortion	IM_3	Note 1	dBc	-42	-45	–
Channel-Temperature Rise	ΔT_{ch}	$V_{DS} \times I_{DS} \times R_{th(c-c)}$	$^\circ\text{C}$	–	–	80

Electrical Characteristics ($T_a = 25^\circ\text{C}$)

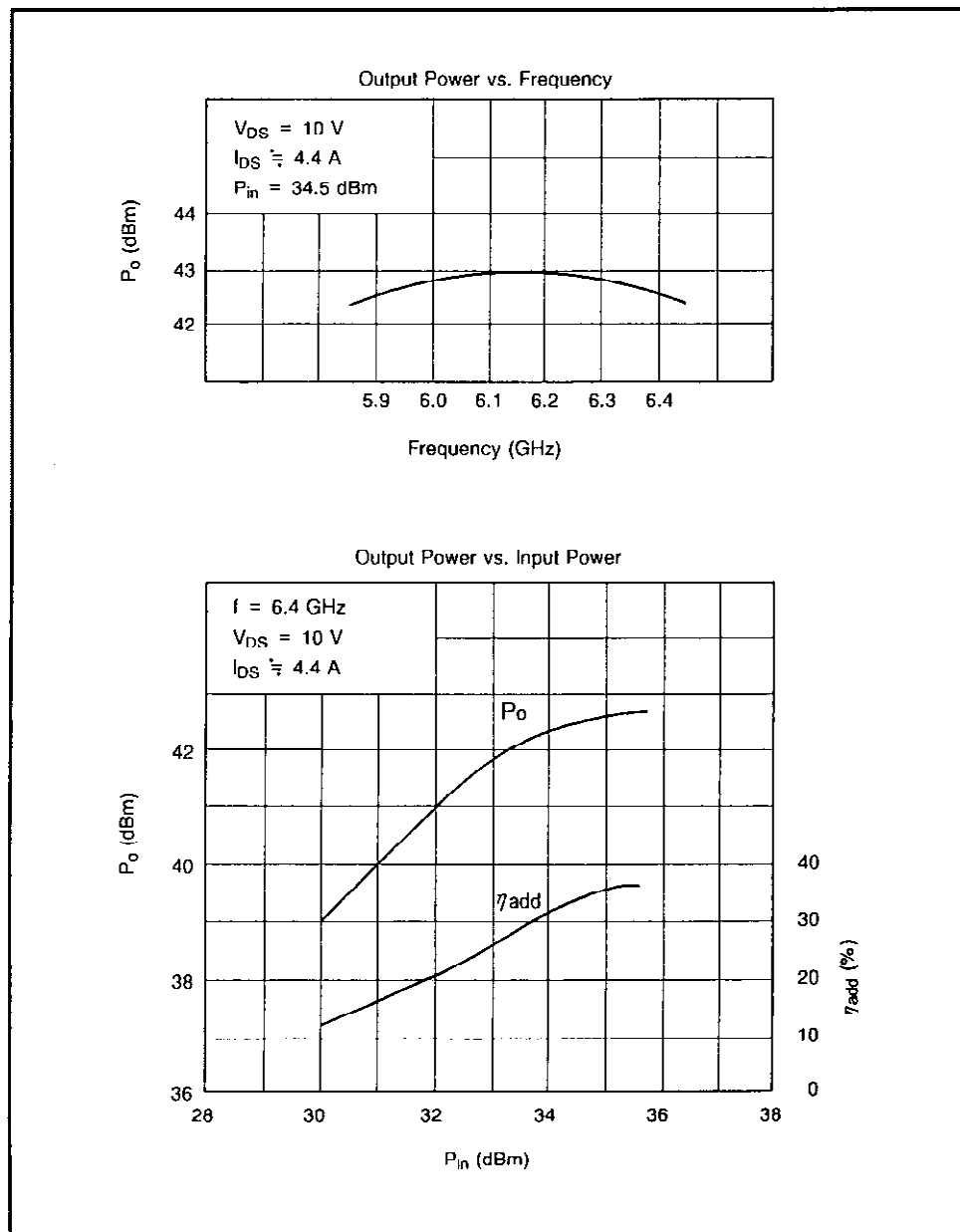
Characteristic	Symbol	Condition	Unit	Min.	Typ.	Max.
Transconductance	gm	$V_{DS} = 3V$ $I_{DS} = 6.0A$	mS	–	3600	–
Pinch-off Voltage	V_{GSoff}	$V_{DS} = 3V$ $I_{DS} = 60$ mA	V	-1	-2.5	-4.0
Saturated Drain Current	I_{DSS}	$V_{DS} = 3V$ $V_{GS} = 0V$	A	–	10.5	14.0
Gate-Source Breakdown Voltage	V_{GSO}	$I_{GS} = -200$ μA	V	-5	–	–
Thermal Resistance	$R_{th(c-c)}$	Channel to Case	$^\circ\text{C/W}$	–	1.5	2.0

Note 1: 2-tone Test Pout = 31.5 dBm Single Carrier Level.

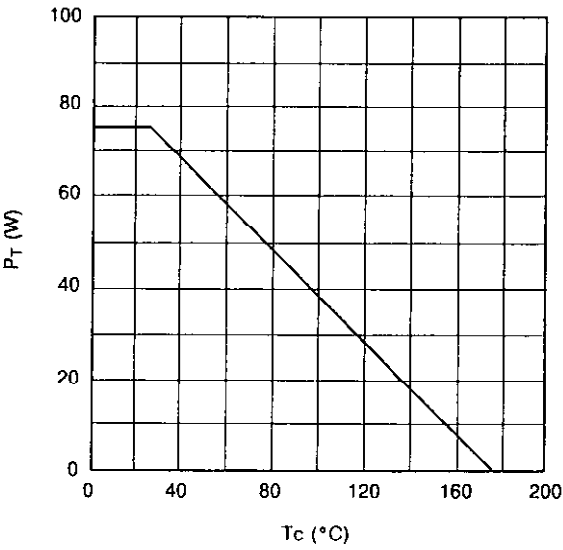
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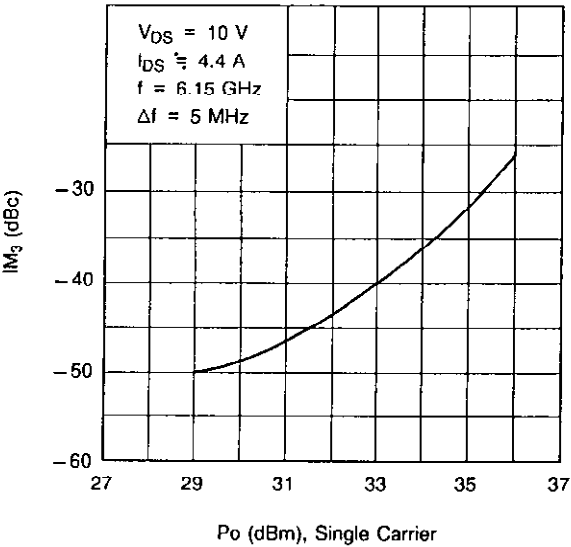
RF Performances



Power Dissipation vs. Case Temperature



IM₃ vs. Output Power Characteristics



TIM5964-16SL S-Parameters (Magn. and Angles)

 $V_{DS} = 10V$, $I_{DS} = 4.0A$ $f = 5.7 \sim 6.6GHz$ 